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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/768,471	01/25/2001	Shinichi Minami	843.39542X00	3956
20457 7	590 06/21/2002			
ANTONELLI TERRY STOUT AND KRAUS SUITE 1800 1300 NORTH SEVENTEENTH STREET			EXAMINER	
			BAUMEISTER, BRADLEY W	
ARLINGTON,	, VA 22209		ART UNIT	PAPER NUMBER
•			2815	
			DATE MAILED: 06/21/2002	

Please find below and/or attached an Office communication concerning this application or proceeding.



Office Action Summary

Application No. **09/768,471**

Applicant(s)

Examiner

B. William Baumeister

Art Unit 2815

Minami et al.



	The MAILING DATE of this communication appears	on the cover sheet with the correspondence address				
	for Reply					
A SHO	A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM					
- Extens	THE MAILING DATE OF THIS COMMUNICATION. Extensions of time may be available under the provisions of 37 CFR 1.136 (a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the					
mailing	date of this communication. eriod for reply specified above is less than thirty (30) days, a reply within th					
- If NO p	period for reply is specified above, the maximum statutory period will apply a	and will expire SIX (6) MONTHS from the mailing date of this communication.				
- Any rep	to reply within the set or extended period for reply will, by statute, cause the ply received by the Office later than three months after the mailing date of t					
Status	patent term adjustment. See 37 CFR 1.704(b).					
	Responsive to communication(s) filed on Apr 26, 2					
2a) 🗌	This action is FINAL . 2b) ✓ This act	ion is non-final.				
3) 🗆	Since this application is in condition for allowance eclosed in accordance with the practice under Ex pair	except for formal matters, prosecution as to the merits is reference Quayle, 1935 C.D. 11; 453 O.G. 213.				
Disposit	tion of Claims					
4) 💢	Claim(s) <u>1-11 and 15-36</u>	is/are pending in the application.				
4	a) Of the above, claim(s) <u>4-11, 15-21, and 23</u>	is/are withdrawn from consideration.				
5) 🗆	Claim(s)	is/are allowed.				
6) 💢	Claim(s) 1-3, 22, and 24-36	is/are rejected.				
7) 🗌	Claim(s)	is/are objected to.				
8) 🗆	Claims	are subject to restriction and/or election requirement.				
Applicat	tion Papers					
9) 🗆	The specification is objected to by the Examiner.					
10) ☐ The drawing(s) filed on is/are a) ☐ accepted or b) ☐ objected to by the Examiner.						
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
11)	The proposed drawing correction filed on	is: a) \square approved b) \square disapproved by the Examiner.				
	If approved, corrected drawings are required in reply t	o this Office action.				
12)	The oath or declaration is objected to by the Exami	ner.				
Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgement is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a) ☑ All b) ☐ Some* c) ☐ None of:						
1	1. 💢 Certified copies of the priority documents have been received.					
2	$2.\square$ Certified copies of the priority documents have	e been received in Application No				
3	3. Copies of the certified copies of the priority do application from the International Burea	ocuments have been received in this National Stage au (PCT Rule 17.2(a)).				
*Se	e the attached detailed Office action for a list of the	e certified copies not received.				
14) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. § 119(e).						
a) The translation of the foreign language provisional application has been received.						
15) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.						
Attachme						
$\stackrel{\sim}{-}$	ice of References Cited (PTO-892)	4) Interview Summary (PTO-413) Paper No(s).				
_	ice of Draftsperson's Patent Drawing Review (PTO-948) Imation Disclosure Statement(s) (PTO-1449) Paper No(s)2	5) Notice of Informal Patent Application (PTO-152)				
3/ (X) 11110	imation disclosure Statement(s) (F10-1449) Paper No(s).	6) Other:				

Application/Control Number: 09/768,471 Page 2

Art Unit: 2815

DETAILED ACTION

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Election/Restriction

2. Applicant's election without traverse of invention IA in Paper No. 10 is acknowledged.

Claim Rejections - 35 U.S.C. § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 4. Claims 1-3, 22, 24, 26, 27, and 29-35 are rejected under 35 U.S.C. 102(b) as being anticipated by Vinn et al. '114. (Applicant uses different terminology to reference a given region in various claim sets. The following rejection will use the terminology employed in claim 1.)
- a. See FIGs 1 and 2 wherein Vinn depicts a Zener diode 10 comprising an n-type epitaxial substrate 14 doped 10e15; a first, p-type region 40,16,18; a second, n-type region 20 doped 10e20 formed under a central sub-portion of the first, p-type region; a plurality of contact

Application/Control Number: 09/768,471 Page 3

Art Unit: 2815

holes 42,44 pass through oxide insulation 47 for electrically connecting conductors in a portion of the first semiconductor region that is outside of the first/second region junction. The portions 16, 18 of the first, p-type semiconductor region extend to a depth deeper than the portion of the p-type region that forms a junction with the n-type region 20.

b. Regarding claims 31 and 34, under the broadest reasonable interpretation, "surrounding" can be interpreted to mean two regions formed on either side of a third region. As such, P regions 16 and 18 and overlying holes associated with contacts 42 and 44 "surround" the pn junction region.

Claim Rejections - 35 U.S.C. § 103

- 5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. Claims 1-3, 22, 24-36 are rejected under 35 U.S.C. 103(a) as being unpatentable over Howard, Jr. '179 in view of Matthews '554.
- a. Howard teaches a zener diode having a p substrate 14; a p well 21; a p+region 22 having the upper portion disposed within p-well 21; and an n-region 32 forming a pn junction with p+ region 22. N region 32 has a wider cross-section than does p+ region 22. Further, n-region

Application/Control Number: 09/768,471 Page 4

Art Unit: 2815

has a peripheral portion with a larger cross-section (greater diffusion depth) than the central pnjunction portion for the purpose of preventing spike-through (col. 5, lines 25-45) when a cathode
contact C is formed though the overlying insulation. Thus, Howard teaches every limitation of
the claims except for the recitation that the peripheral region has a plurality of through holes.

Rather, Howard only discloses a single through hole extending along one side of the n-type region
32 periphery.

b. Matthews, directed towards a zener protection circuit, teaches that a plurality of uniformly spaced vias may be employed for each of the p and n regions for the purpose of providing uniform current distribution, thereby preventing high current densities and premature failure (col. 3, lines 35-45). Thus, it would have been obvious to one of ordinary skill in the art at the time of the invention to have provided the Howard zener diode with a plurality of through holes in the insulation layer distributed to surround the periphery of the n-region 32 for the purpose of providing better current distribution, and thereby preventing high current densities and premature failure as taught by Matthews.

Conclusion

- 7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
 - a. JP 63-66974 teaches a zener diode having leads with a plurality of through-holes.

Art Unit: 2815

- b. Ohuchi et al. '579 teaches an n/n-/n/p+ reverse-bias avalanche diode with contacts to guard-ring regions that prevent surface breakdown.
- c. GB '792 teaches a zener diode with peripheral n+ regions of greater diffusion depth than that of the central region.
 - d. Doluca '165 teaches a buried zener diode.
 - e. Villa et al. '387 teaches a zener diode.
 - f. Beasom '503 teaches a zener diode. See particularly FIG 8.
 - g. Muggli '114 teaches a subsurface breakdown zener diode.

INFORMATION ON HOW TO CONTACT THE USPTO

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to the examiner, **B. William Baumeister**, at (703) 306-9165. The examiner can normally be reached Monday through Friday, 8:30 a.m. to 5:00 p.m. If the Examiner is not available, the Examiner's supervisor, Mr. Eddie Lee, can be reached at (703) 308-1690. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0956.

B. William Baumeister

Patent Examiner, Art Unit 2815

June 20, 2002